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SLOVENSKI STANDARD
SIST EN 60749-23:2004/A1:2011

01-maj-2011

Polprevodniški elementi - Metode za mehansko in klimatsko preskušanje - 23. del: Obratovalna življenjska doba pri visoki temperaturi - Dopolnilo A1 (IEC 60749-23:2004/A1:2011)

Semiconductor devices - Mechanical and climatic test methods - Part 23: High temperature operating life (IEC 60749-23:2004/A1:2011)

Halbleiterbauelemente - Mechanische und klimatische Prüfverfahren - Teil 23: Lebensdauer bei hoher Temperatur (IEC 60749-23:2004/A1:2011)

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Dispositifs à semiconducteurs - Méthodes d'essais mécaniques et climatiques - Partie 23: Durée de vie en fonctionnemement à haute température (CEI 60749-23:2004/A1:2011)

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Ta slovenski standard je istoveten z: **EN 60749-23:2004/A1:2011**

ICS:

31.080.01	Polprevodniški elementi (naprave) na splošno	Semiconductor devices in general

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2003-01.Slovenski inštitut za standardizacijo. Razmnoževanje celote ali delov tega standarda ni dovoljeno.

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EUROPEAN STANDARD

NORME EUROPÉENNE

EUROPÄISCHE NORM

EN 60749-23/A1

March 2011

ICS 31.080.01

English version

Semiconductor devices - Mechanical and climatic test methods - Part 23: High temperature operating life (IEC 60749-23:2004/A1:2011)

Dispositifs à semiconducteurs -
Méthodes d'essais mécaniques et climatiques -
Partie 23: Durée de vie en fonctionnement à haute température
(CEI 60749-23:2004/A1:2011)

Halbleiterbauelemente -
Mechanische und klimatische Prüfverfahren -
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This amendment A1 modifies the European Standard EN 60749-23:2004; it was approved by CENELEC on 2011-03-03. CENELEC members are bound to comply with the CEN/CENELEC Internal Regulations which stipulate the conditions for giving this amendment the status of a national standard without any alteration.

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Up-to-date lists and bibliographical references concerning such national standards may be obtained on application to the Central Secretariat or to any CENELEC member.

This amendment exists in three official versions (English, French, German). A version in any other language made by translation under the responsibility of a CENELEC member into its own language and notified to the Central Secretariat has the same status as the official versions.

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CENELEC

European Committee for Electrotechnical Standardization
Comité Européen de Normalisation Electrotechnique
Europäisches Komitee für Elektrotechnische Normung

Management Centre: Avenue Marnix 17, B - 1000 Brussels

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Foreword

The text of document 47/2017/CDV, future amendment 1 to IEC 60749-23:2004, prepared by IEC TC 47, Semiconductor devices, was submitted to the IEC-CENELEC parallel vote and was approved by CENELEC as amendment A1 to EN 60749-23:2004 on 2011-03-03.

Attention is drawn to the possibility that some of the elements of this document may be the subject of patent rights. CEN and CENELEC shall not be held responsible for identifying any or all such patent rights.

The following dates were fixed:

– latest date by which the amendment has to be implemented at national level by publication of an identical national standard or by endorsement	(dop)	2011-12-03
– latest date by which the national standards conflicting with the amendment have to be withdrawn	(dow)	2014-03-03

Endorsement notice

The text of amendment 1:2011 to the International Standard IEC 60749-23:2004 was approved by CENELEC as an amendment to the European Standard without any modification.

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INTERNATIONAL STANDARD

NORME INTERNATIONALE

AMENDMENT 1
AMENDEMENT 1

Semiconductor devices – Mechanical and climatic test methods –
Part 23: High temperature operating life

Dispositifs à semiconducteurs – Méthodes d'essais mécaniques et climatiques –
Partie 23: Durée de vie en fonctionnement à haute température

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FOREWORD

This amendment has been prepared by IEC technical committee 47: Semiconductor devices.

The text of this amendment is based on the following documents:

CDV	Report on voting
47/2017/CDV	47/2074/RVC

Full information on the voting for the approval of this amendment can be found in the report on voting indicated in the above table.

The committee has decided that the contents of this publication will remain unchanged until the stability date indicated on the IEC web site under "http://webstore.iec.ch" in the data related to the specific publication. At this date, the publication will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

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7 Measurements

Delete the last sentence of this clause ("This and the high temperature testing restrictions…*") and Note 1.*

Add the following new paragraph:

If the devices have been removed from bias and the 96 hour window is exceeded, the stress shall be resumed for the duration specified in Table 1 prior to completion of the measurements. After an interim measurement, the stress shall be continued from the point of interruption. This and the high temperature testing restrictions of this clause need not be met if verification data for a given technology is provided."

Renumber the existing Note 2 as Note.

Add the following table after the Note:

SIST EN 60749-23:2004/A1:2011

Table 1 – Additional stress requirements for parts not tested within 96 h

	Hours by which 96 h window has been exceeded			
	>0 but ≤168	**>168 but ≤336**	**>336 but ≤504**	**Other**
Additional stress hours required prior to performing electrical test	24	48	72	24 h for each 168 h (week) by which the 96 h window has been exceeded

9 Summary

Replace, in item f), the reference to "Clause 6" by "Clause 7".

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